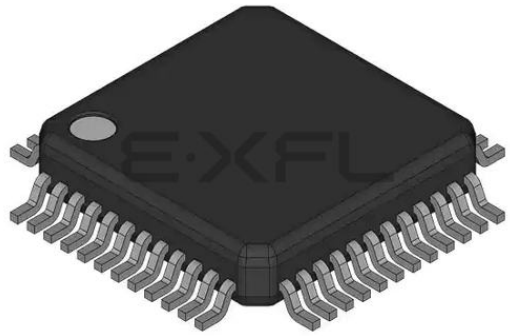

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	SCI, SPI
Peripherals	DMA, LVD, PWM, WDT
Number of I/O	39
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mcf51ag96clf

Table 1. MCF51AG128 Series Device Comparison (continued)

Feature	MCF51AG128			MCF51AG96		
	80-pin	64-pin	48-pin	80-pin	64-pin	48-pin
TPM3 (timer pulse-width modulator) channels	2					
Debug Visibility Bus	Yes	No	No	Yes	No	No

[1] Up to 16 pins on Ports E and F are shared with the ColdFire Rapid GPIO module.

[2] Some pins of FTMx might not be bonded on small package, therefore these channels could be used as soft timer only.

1.2 Block Diagram

Figure 1 shows the connections between the MCF51AG128 series pins and modules.

Table 2. MCF51AG128 Series Functional Units (continued)

Functional Unit	Function
WDOG (Watchdog timer)	keeps a watch on the system functioning and resets it in case of its failure
RTC (Real Time Counter)	Provides a constant time-base with optional interrupt

Figure 4 shows the pinout of the 48-pin LQFP.

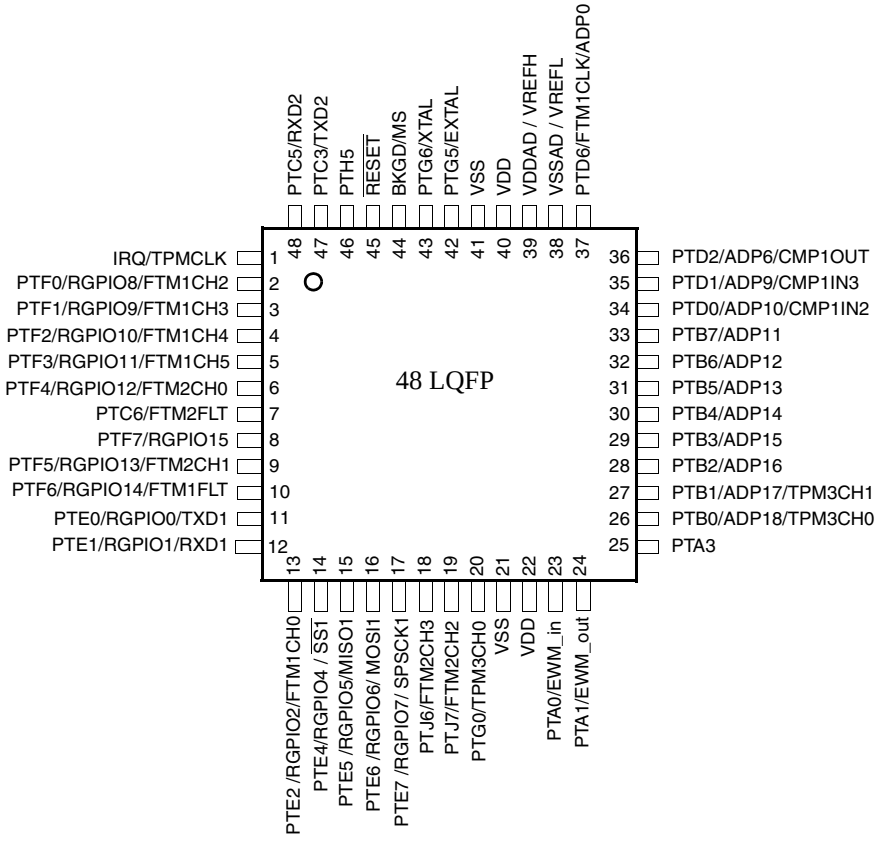


Figure 4. 48-Pin LQFP

Table 5. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to 5.8	V
Input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	±25	mA
Maximum current into V_{DD}	I_{DD}	120	mA
Storage temperature	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low which would reduce overall power consumption.

2.3 Thermal Characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} is very small.

Table 6. Thermal Characteristics

Rating		Symbol	Value	Unit
Operating temperature range (packaged)		T_A	–40 to 105	°C
Maximum junction temperature		T_J	150	°C
Thermal resistance [1,2,3,4]				
80-pin LQFP				
	1s	θ_{JA}	56	°C/W
	2s2p		45	
64-pin QFP				
	1s		54	
	2s2p		41	
64-pin LQFP				
	1s		67	
	2s2p		49	
48-pin LQFP				
	1s		69	
	2s2p		51	

1 Typical values are based on characterization data at 25°C unless otherwise stated.

2 Measured with $V_{In} = V_{DD}$ or V_{SS}.

3 Measured with $V_{In} = V_{SS}$.

4 Measured with $V_{In} = V_{DD}$.

5 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).

6 All functional non-supply pins are internally clamped to V_{SS} and V_{DD}.

7 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values.

8 The $\overline{\text{RESET}}$ pin does not have a clamp diode to V_{DD}. Do not drive this pin above V_{DD}.

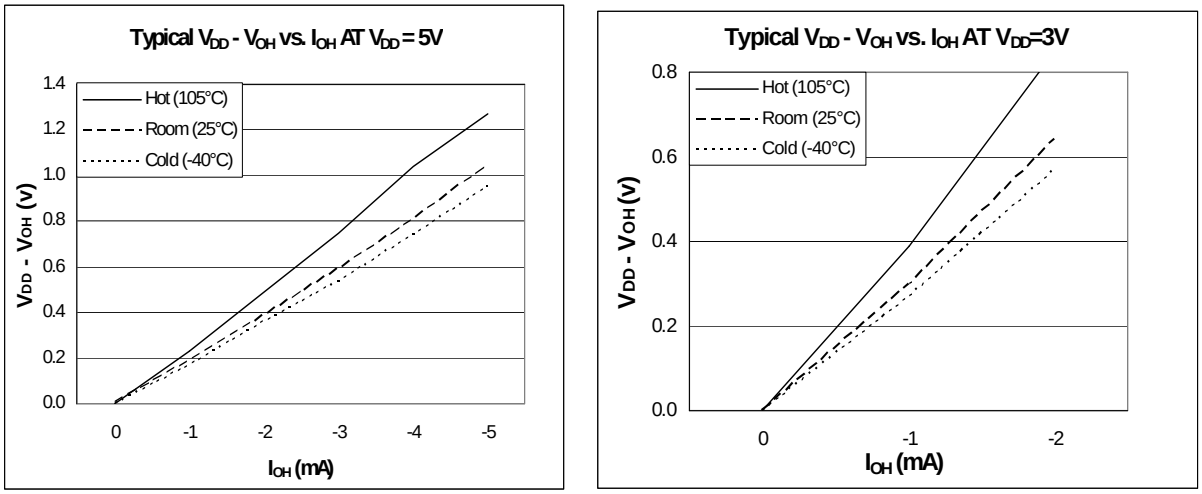


Figure 5. Typical I_{OH} vs. $V_{DD} – V_{OH}$ (Low Drive,PTxDSn = 0)

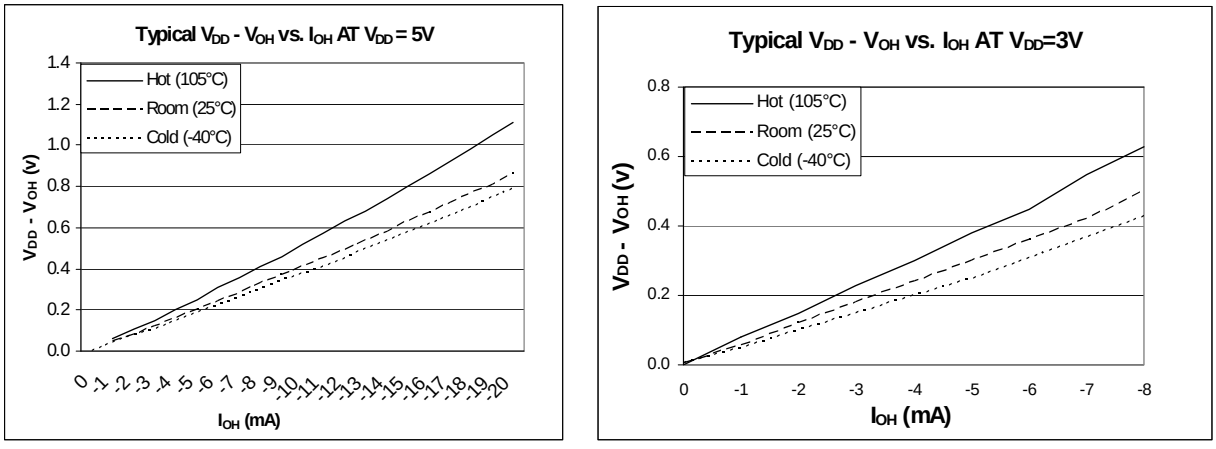


Figure 6. Typical I_{OH} vs. $V_{DD} – V_{OH}$ (High Drive, PTxDSn = 1)

2.6 Supply Current Characteristics

Table 10. Supply Current Characteristics

Num	C	Parameter	Symbol	V_{DD} (V)	Typical[1]	Max[2]	Unit
1	C	Run supply current[3] measured at 4 MHz CPU clock (All Peripheral Clocks are ON)	RI_{DD}	5	5.8	7	mA
				3	5.7	7	
2	C	Run supply current[3] measured at 16 MHz CPU clock (All Peripheral Clocks are ON)		5	21	25	mA
				3	20.9	25	
3	C	Run supply current[3] measured at 32 MHz CPU clock (All Peripheral Clocks are ON)		5	39.2	50	mA
				3	39.1	50	
4	P	Run supply current[3] measured at 50MHz CPU clock (All Peripheral Clocks are ON)		5	57.9	70	mA
				3	57.8	70	
5	C	Run supply current[3] measured at 4 MHz CPU clock (All Peripheral Clocks are OFF[4])	RI_{DD}	5	4.7	6	mA
				3	4.6	6	
6	C	Run supply current[3] measured at 16 MHz CPU clock (All Peripheral Clocks are OFF[4])		5	16.1	20	mA
				3	15.9	20	
7	C	Run supply current[3] measured at 32 MHz CPU clock (All Peripheral Clocks are OFF[4])		5	29	35	mA
				3	28.9	35	
8	C	Run supply current[3] measured at 50 MHz CPU clock (All Peripheral Clocks are OFF[4])		5	44.1	50	mA
				3	44.0	50	
9	C	Wait supply current[3] measured at 4 MHz CPU clock	WI_{DD}	5	3.2	5	mA
				3	3.2	5	
10	C	Wait supply current[3] measured at 16 MHz CPU clock		5	10.1	13	mA
				3	10	13	
11	C	Wait supply current[3] measured at 32 MHz CPU clock		5	19	25	mA
				3	18.8	25	
12	C	Wait supply current[3] measured at 50 MHz CPU clock		5	29.2	40	mA
				3	29	40	
13	C P C	Stop2 mode supply current –40 °C 25 °C 105 °C	$S2I_{DD}$	5	 1.17 1.35 28.6	 3 3 40	µA
	C P C	–40 °C 25 °C 105 °C		3	1.0 1.34 26.8	3 3 40	µA

2.7 High Speed Comparator (HSCMP) Electricals

Table 11. HSCMP Electrical Specifications

Num	C	Rating	Symbol	Min	Typical	Max	Unit
1	—	Supply voltage	V_{DD}	2.7	—	5.5	V
2	T	Supply current, high speed mode (EN = 1, PMODE = 1)	I_{DDAHS}	—	200	—	μA
3	T	Supply current, low speed mode (EN = 1, PMODE = 0)	I_{DDALS}	—	20	—	μA
4	—	Analog input voltage	V_{AIN}	V_{SS} – 0.3	—	V_{DD}	V
5	D	Analog input offset voltage	V_{AIO}	—	5	40	mV
6	D	Analog Comparator hysteresis	V_H	3.0	9.0	20.0	mV
7	D	Propagation delay, high speed mode (EN = 1, PMODE = 1)	t_{DHS}	—	70	120	ns
8	D	Propagation delay, low speed mode (EN = 1, PMODE = 0)	t_{DLS}	—	400	600	ns
9	D	Analog Comparator initialization delay	t_{AINIT}	—	400	—	ns

2.8 Digital to Analog (DAC) Characteristics

Num	C	Rating	Symbol	Min	Typical	Max	Unit
1	D	Supply voltage	V_{DDA}	2.7	—	5.5	V
2	D	Supply current (enabled)	I_{DDAC}	—	—	20	μA
3	D	Supply current (stand-by)	I_{DDACS}	—	—	150	nA
4	D	DAC reference input voltage	V_{in1}, V_{in2}	V_{SSA}	—	V_{DDA}	V
5	D	DAC setup delay	t_{PRGST}	—	1000	—	nS
6	D	DAC step size	V_{step}	$3V_{in}/128$	$V_{in}/32$	$5V_{in}/128$	V
7	D	DAC output voltage range	V_{dacout}	$V_{in}/32$	—	V_{in}	V
8	P	Bandgap voltage reference factory trimmed at V_{DD} = 5 V, Temp = 25 °C	V_{BG}	1.18	1.20	1.21	V

2.9 ADC Characteristics

Table 12. 5V 12-bit ADC Operating Conditions

Num	C	Characteristic	Conditions	Symb	Min	Typical[1]	Max	Unit	Comment
1	D	Supply voltage	Absolute	V_{DDA}	2.7	—	5.5	V	—
			Delta to V_{DD} (V_{DD}–V_{DDA})[2]	ΔV_{DDA}	–100	0	100	mV	—
2	D	Ground voltage	Delta to V_{SS} (V_{SS}–V_{SSA})[2]	ΔV_{SSA}	–100	0	100	mV	—

Table 12. 5V 12-bit ADC Operating Conditions (continued)

Num	C	Characteristic	Conditions	Symb	Min	Typical[1]	Max	Unit	Comment
3	D	Ref Voltage High	—	V_{REFH}	2.7	V_{DDA}	V_{DDA}	V	—
4	D	Ref Voltage Low	—	V_{REFL}	V_{SSAD}	V_{SSA}	V_{SSA}	V	—
5	D	Input Voltage	—	V_{ADIN}	V_{REFL}	—	V_{REFH}	V	—
6	C	Input Capacitance	—	C_{ADIN}	—	4.5	5.5	pF	—
7	C	Input Resistance	—	R_{ADIN}	—	3	5	kΩ	—
8	C	Analog Source Resistance	12 bit mode f_{ADCK} > 4 MHz f_{ADCK} < 4 MHz	R_{AS}	 — —	 — —	 2 5	kΩ	External to MCU
	C		10 bit mode f_{ADCK} > 4 MHz f_{ADCK} < 4 MHz		 — —	 — —	 5 10		
	C		8 bit mode (all valid f_{ADCK})		—	—	10		
9	D	ADC Conversion Clock Freq.	High Speed (ADLPC = 0)	f_{ADCK}	0.4	—	8.0	MHz	—
	D		Low Power (ADLPC = 1)		0.4	—	4.0		—

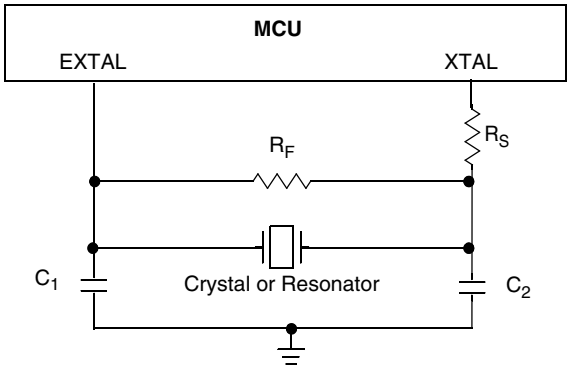
1 Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

2 DC potential difference.

2 When MCG is configured for FEE or FBE mode, input clock source must be divisible using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

3 This parameter is characterized and not tested on each device. Proper PC board layout procedures must be followed to achieve specifications.

4 4 MHz crystal



2.11 ICS Specifications

Table 15. ICS Frequency Specifications (Temperature Range = –40 to 105 °C Ambient)

Num	C	Rating		Symbol	Min	Typical[1]	Max	Unit
1	C	Internal reference frequency - factory trimmed at V_{DD} = 5 V and temperature = 25 °C		f_{int_ft}	—	32.768	—	kHz
2	C	Average internal reference frequency – untrimmed		f_{int_ut}	31.25	—	39.06	kHz
3	T	Internal reference startup time		t_{irefst}	—	60	100	µs
4	C	DCO output frequency range - untrimmed [2]	Low range (DRS = 00)	f_{dco_ut}	16	—	20	MHz
	C		Mid range (DRS = 01)		32	—	40	
	C		High range (DRS = 10)		48	—	60	
5	P	DCO output frequency[2] Reference =32768Hz and DMX32 = 1	Low range (DRS = 00)	f_{dco_DMX32}	—	16.82	—	MHz
	P		Mid range (DRS = 01)		—	33.69	—	
	P		High range (DRS = 10)		—	50.48	—	
6	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (using FTRIM)		$\Delta f_{dco\_res\_t}$	—	±0.1	±0.2	$\%f_{dco}$
7	D	Resolution of trimmed DCO output frequency at fixed voltage and temperature (not using FTRIM)		$\Delta f_{dco\_res\_t}$	—	±0.2	±0.4	$\%f_{dco}$
8	D	Total deviation of trimmed DCO output frequency over full voltage and temperature range		Δf_{dco_t}	—	0.5 –1.0	±2	$\%f_{dco}$
9	D	Total deviation of trimmed DCO output frequency over fixed voltage and temperature range of 0 –70 °C		Δf_{dco_t}	—	±0.5	±1	$\%f_{dco}$

Table 15. ICS Frequency Specifications (continued)(Temperature Range = –40 to 105 °C Ambient)

Num	C	Rating	Symbol	Min	Typical[1]	Max	Unit
10	D	FLL acquisition time [3]	$t_{fll\_acquire}$	—	—	1	ms
11	D	Long term Jitter of DCO output clock (averaged over 2ms interval) [4]	C_{Jitter}	—	0.02	0.2	$\%f_{dco}$
12	D	Loss of external clock minimum freq. (RANGE = 0) • ext. clock freq: above $(3/5)f_{int}$, never reset • ext. clock freq: between $(2/5)f_{int}$ and $(3/5)f_{int}$, maybe reset (phase dependency) • ext. clock freq: below $(2/5)f_{int}$, always reset	f_{loc_low}	$(3/5) \times f_{int}$	—	—	kHz
13	D	Loss of external clock minimum freq. (RANGE = 1) • ext. clock freq: above $(16/5)f_{int}$, never reset • ext. clock freq: between $(15/5)f_{int}$ and $(16/5)f_{int}$, maybe reset (phase dependency) • ext. clock freq: below $(15/5)f_{int}$, always reset	f_{loc_high}	$(16/5) \times f_{int}$	—	—	kHz

1 Data in Typical column was characterized at 3.0 V, 25 °C or is typical recommended value

2 The resulting bus clock frequency should not exceed the maximum specified bus clock frequency of the device.

3 This specification applies to any time the FLL reference source or reference divider is changed, trim value changed or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

4 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{BUS}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the FLL circuitry by V_{DD} and V_{SS} and variation in crystal oscillator frequency increase the C_{Jitter} percentage for a given interval.

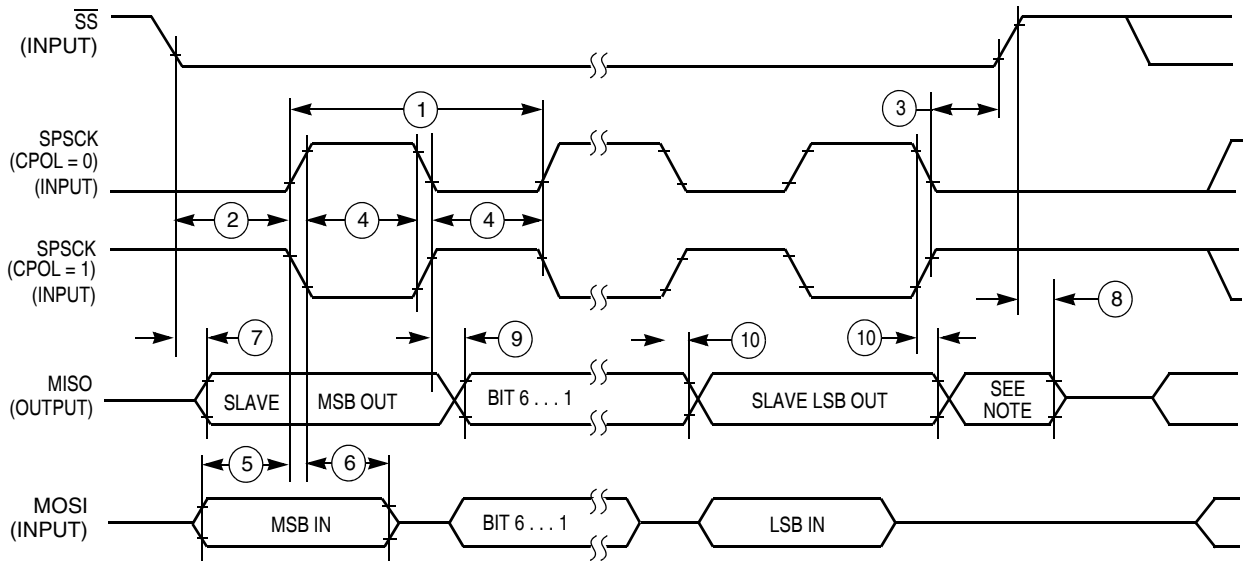
2.12.3 SPI Characteristics

Table 18 and Figure 15 through Figure 18 describe the timing requirements for the SPI system.

Table 18. SPI Timing Characteristics

No.	C	Function	Symbol	Min	Max	Unit
—	D	Operating frequency Master Slave	f_{op}	$f_{Bus}/2048$ 0	$f_{Bus}/2$ $f_{Bus}/4$	Hz
1	D	SPSCK period Master Slave	t_{SPSCK}	2 4	2048 —	t_{cyc} t_{cyc}
2	D	Enable lead time Master Slave	t_{Lead}	1/2 1	— —	t_{SPSCK} t_{cyc}
3	D	Enable lag time Master Slave	t_{Lag}	1/2 1	— —	t_{SPSCK} t_{cyc}
4	D	Clock (SPSCK) high or low time Master Slave	t_{WSPSCK}	$t_{cyc} - 30$ $t_{cyc} - 30$	1024 t_{cyc} —	ns ns
5	D	Data setup time (inputs) Master Slave	t_{SU}	30 30	— —	ns ns
6	D	Data hold time (inputs) Master Slave	t_{HI}	10 10	— —	ns ns
7	D	Slave access time	t_a	—	—	t_{cyc}
8	D	Slave MISO disable time	t_{dis}	—	—	t_{cyc}
9	D	Data valid time (maximum delay after SPCLK edge to Data output) Master Slave	t_V[1]	 — —	 25 70	 ns ns
10	D	Data hold time (minimum delay after SPCLK edge to Data output) Master Slave	t_{HO}[1]	 10 10	 — —	 ns ns

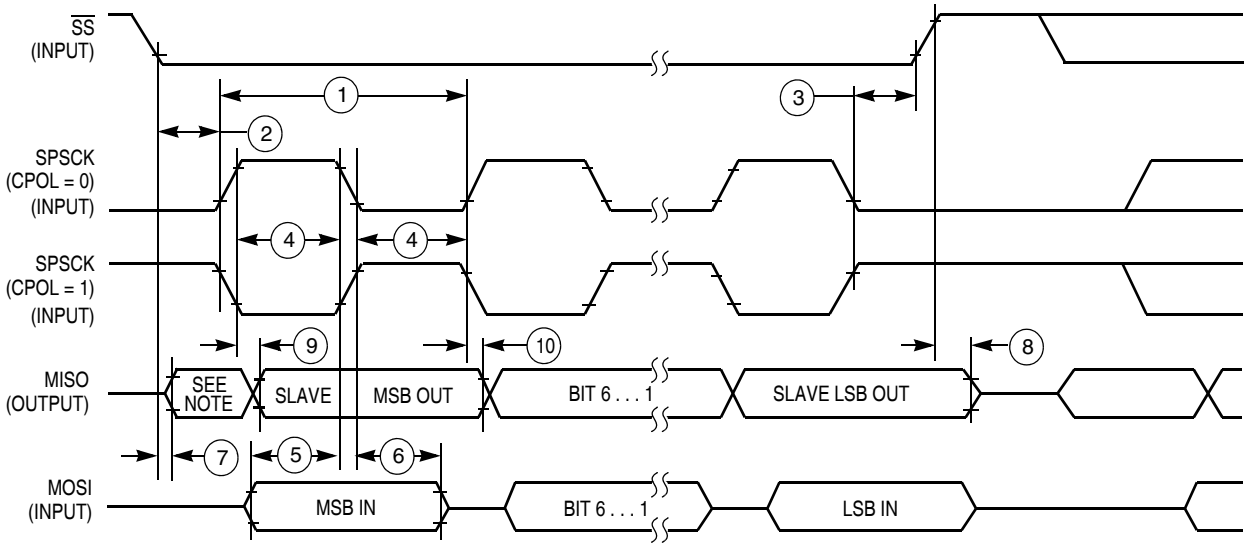
[1] SPI Output Load = 30 pf



NOTE:

1. Not defined but normally MSB of character just received

Figure 17. SPI Slave Timing (CPHA = 0)



NOTE:

1. Not defined but normally LSB of character just received

Figure 18. SPI Slave Timing (CPHA = 1)

2.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the Flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see *MCF51AG128 Reference Manual*.

Table 19. Flash Characteristics

Num	C	Characteristic	Symbol	Min	Typical[1]	Max	Unit
1	—	Supply voltage for program/erase	$V_{prog/erase}$	2.7		5.5	V
2	—	Supply voltage for read operation	V_{Read}	2.7		5.5	V
3	—	Internal FCLK frequency[2]	f_{FCLK}	150		200	kHz
4	—	Internal FCLK period (1/FCLK)	t_{Fcyc}	5		6.67	µs
5	—	Byte program time (random location)[2]	t_{prog}	9			t_{Fcyc}
6	—	Byte program time (burst mode)[2]	t_{Burst}	4			t_{Fcyc}
7	—	Page erase time[3]	t_{Page}	4000			t_{Fcyc}
8	—	Mass erase time[2]	t_{Mass}	20,000			t_{Fcyc}
9	C	Program/erase endurance[4] T_L to T_H = –40 °C to 105 °C T = 25 °C		10,000 —	— 100,000	— —	cycles
10	C	Data retention[5]	t_{D_ret}	15	100	—	years

1 Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.

2 The frequency of this clock is controlled by a software setting.

3 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

4 **Typical endurance for flash** was evaluated for this product family on the HC9S12Dx64. For additional information on how Freescale Semiconductor defines typical endurance, please refer to Engineering Bulletin EB619/D, *Typical Endurance for Nonvolatile Memory*.

5 **Typical data retention** values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25 °C using the Arrhenius equation. For additional information on how Freescale Semiconductor defines typical data retention, please refer to Engineering Bulletin EB618/D, *Typical Data Retention for Nonvolatile Memory.*

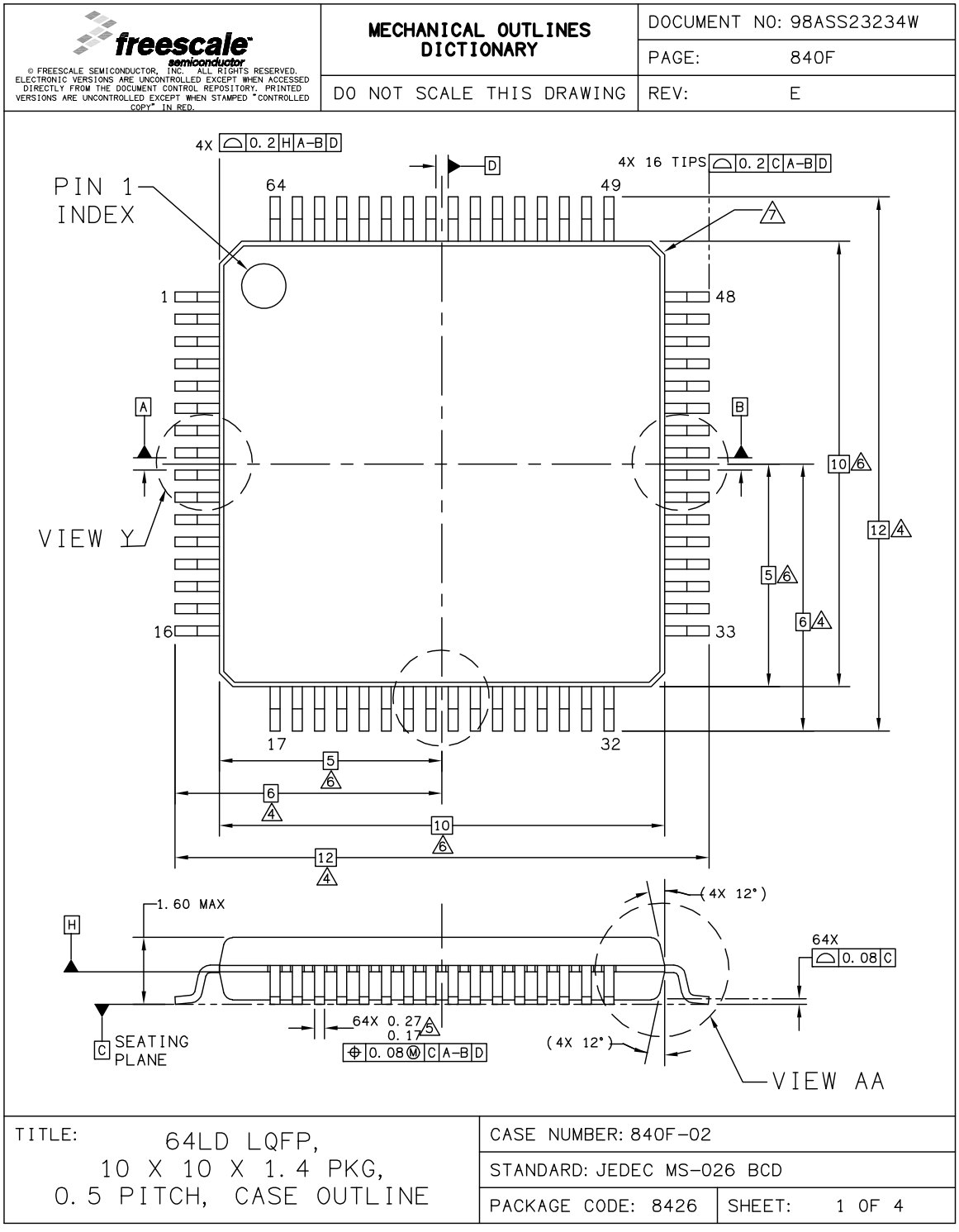
2.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.14.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a custom EMC evaluation board while running specialized EMC test software. The radiated emissions from the microcontroller are measured in a TEM cell in two package orientations (North and East). For more detailed information concerning the evaluation results, conditions and setup, please refer to the EMC Evaluation Report for this device.

5.2 64-pin LQFP Package



freescale semiconductor	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23234W
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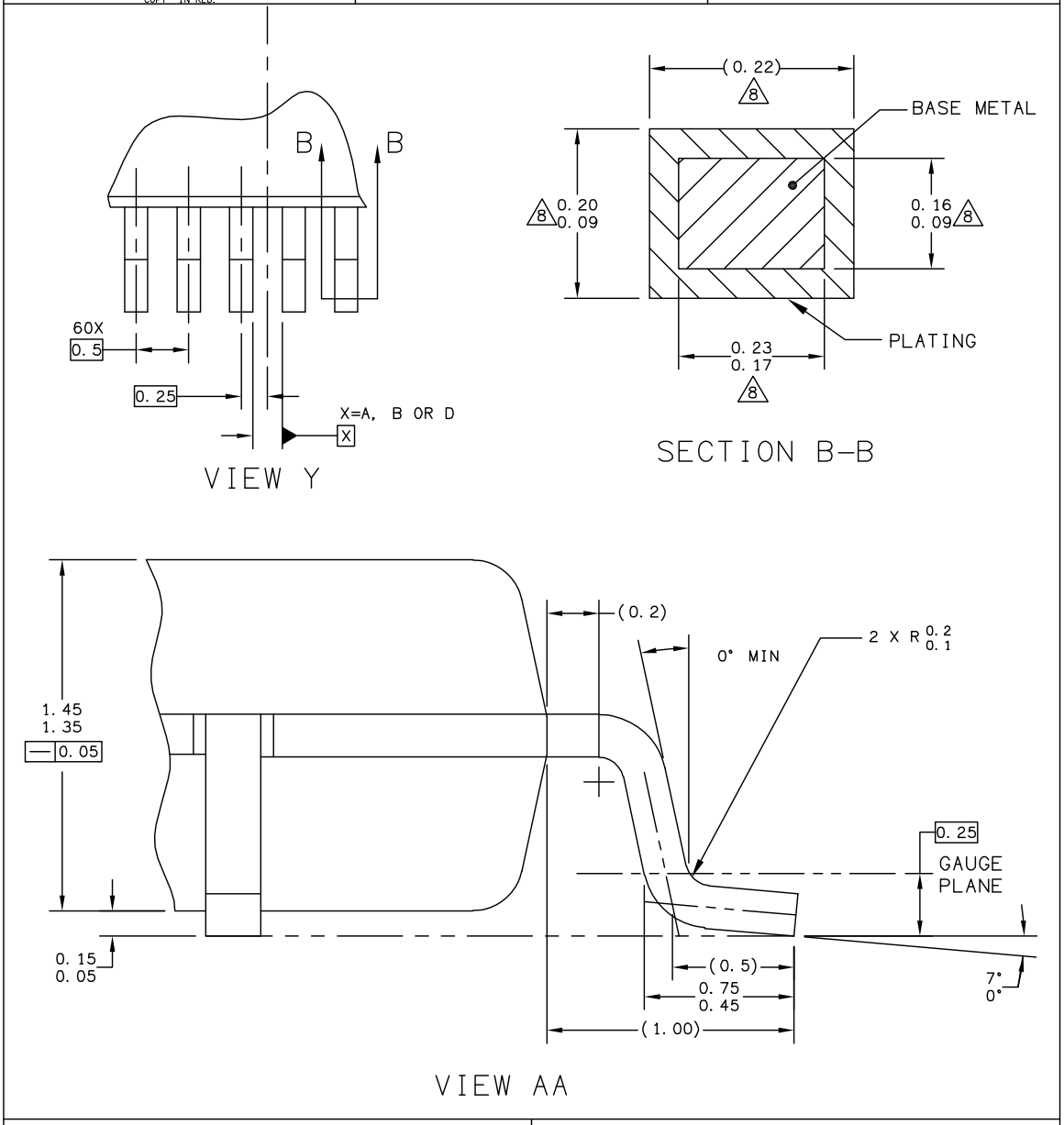

TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	CASE NUMBER: 840F-02	
	STANDARD: JEDEC MS-026 BCD	
	PACKAGE CODE: 8426	SHEET: 2

freescale semiconductor	MECHANICAL OUTLINES DICTIONARY	DOCUMENT NO: 98ASS23234W
		PAGE: 840F
	DO NOT SCALE THIS DRAWING	REV: E

NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994.
3. DATUMS A, B AND D TO BE DETERMINED AT DATUM PLANE H.
4. DIMENSIONS TO BE DETERMINED AT SEATING PLANE C.
5. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE UPPER LIMIT BY MORE THAN 0.08 mm AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD SHALL NOT BE LESS THAN 0.07 mm.
6. THIS DIMENSION DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THIS DIMENSION IS MAXIMUM PLASTIC BODY SIZE DIMENSION INCLUDING MOLD MISMATCH.
7. EXACT SHAPE OF EACH CORNER IS OPTIONAL.
8. THESE DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.1 mm AND 0.25 mm FROM THE LEAD TIP.

TITLE: 64LD LQFP, 10 X 10 X 1.4 PKG, 0.5 PITCH, CASE OUTLINE	CASE NUMBER: 840F–02	
	STANDARD: JEDEC MS–026 BCD	
	PACKAGE CODE: 8426	SHEET: 3

5.4 48-pin LQFP Package

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